

1 **Electronic supplementary information**

2 **Simulation of Conformality of ALD Growth Inside**

3 **Lateral Channels: Comparison Between a Diffusion–Reaction**

4 **Model and a Ballistic Transport–Reaction Model**

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10 **1 Model B: Impact of structure geometry on saturation profiles**

11 Preliminary simulations were performed using the ballistic transport–reaction model to replicate the results
12 presented in the original work by Yanguas-Gil and Elam.¹ Specifically, the goal was to obtain a similar shape
13 at the end of the saturation profile, in a situation where the surface coverage is nearly uniform throughout the
14 structure.

15 The simulation parameters were as in the base case presented in our article, except for the structure
16 aspect ratio and the exposure durations. The simulations were performed using channel and hole geometries
17 (*Trench* and *Via* classes in the *Machball* Python package²), as our article used a channel geometry and the
18 original work by Yanguas-Gil and Elam¹ presented results generated using a hole geometry. To facilitate
19 comparison of the results, the hole equivalent aspect ratios (EAR)³ were identical for both structures. Two
20 series of simulations were performed using each type of structure geometry: a series with varying exposure
21 durations and hole equivalent aspect ratios and a series with varying exposure durations and a constant hole
22 equivalent aspect ratio. In the former series, the hole equivalent aspect ratios were selected to be in the same
23 order of magnitude as in the work by Yanguas-Gil and Elam:¹ 25, 50, 75, 100, 125. In the latter series, the
24 AR of the channel was 1000, as in our article, resulting in an EAR of 500.

25 The exposure duration was varied in all series of simulations. For the series with varying EAR, the
26 suitable exposure durations were estimated using the Gordon *et al.*⁴ model. The hole equivalent aspect ratio,
27 multiplied by 0.9, was inserted in the Gordon *et al.*⁴ model (Ref. 4 Eq. 15) and the exposure duration was
28 solved for. The aspect ratios and exposure durations used are shown in Table S1. For the series with constant
29 EAR, the exposure duration was varied as in our article: 0.01, 0.1, 1, 10 and 100 s.

Table S1 Exposure durations and aspect ratios used in the ballistic transport–reaction model in the series with varying aspect ratios

t (s)	Channel		Hole
	EAR (-)	AR (-)	AR = EAR (-)
0.032	25	50	25
0.12	50	100	50
0.26	75	150	75
0.46	100	200	100
0.71	125	250	125

30 The obtained saturation profiles are shown in Figure S1. In the series with varying channel aspect ratio
31 (Fig. S1a), the saturation profiles show a slight, gentle decrease in surface coverage with penetration into

32 the channel. In the hole geometry, the saturation profiles decrease first and then plateau at the closed end
 33 of the hole, producing a similar shape as the saturation profiles presented by Yanguas-Gil and Elam (Ref. 1
 34 Fig. 3). In the series with constant channel aspect ratio (Fig. S1b), the $t = 1$ s saturation profile shows an
 35 increase in surface coverage, a *trunk*, at the closed end of the channel. This increase in surface coverage was
 36 not observed in the hole geometry.

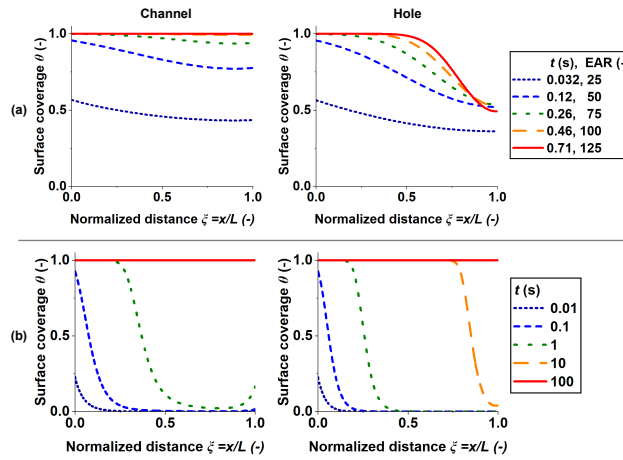


Figure S1 Series of saturation profiles generated using the ballistic transport–reaction model with two structure geometries: (left) channel and (right) hole. In panel (a), the exposure duration and hole equivalent aspect ratio were varied as indicated by the legend. The structure-specific aspect ratios are shown in Table S1. In panel (b), only the exposure duration was varied, while the EAR was constant. At 500, the aspect ratio of the channel and hole was 1000 and 500, respectively. The other simulation parameters were as in the base case presented in our article (Table 2).

37 2 Model B: Examination of view factors

38 The view factors calculated by the ballistic transport–reaction model¹ were investigated to explain the mech-
 39 anism by which resolution affects the simulated saturation profiles. A channel with an aspect ratio of 1000
 40 was discretized into 100, 1000, 2000 and 4000 segments, corresponding to resolutions of 0.1, 1, 2 and 4,
 41 respectively. The view factors between discretization segments were visualized on a two-dimensional raster,
 42 where the view factor between segments is indicated by the colour of the corresponding raster element. In
 43 addition, the impingement probability from the channel entrance and the segment areas were plotted. All of
 44 the values were calculated using the *Machball* Python package.²

45 Figure S2 shows the view factors between discretization segments, the impingement probability distri-

46 bution of a molecule coming from the channel entrance, as well as the areas of the discretization segments.
47 As the resolution (*i.e.* number of discretization segments per aspect ratio unit) is increased, the view factor
48 distribution broadens (Fig. S2, two leftmost columns). Furthermore, the impingement probability from the
49 channel entrance decreases with increasing channel aspect ratio (Fig. S2, third column from left). The area
50 of the channel entrance and end wall is equal to one in each case. However, the areas of the channel side
51 wall segments vary with resolution: when the resolution is below two, the side wall segments are larger
52 than the channel entrance and end wall (Fig. S2, rightmost column). At a resolution of two discretization
53 segments per channel aspect ratio, all areas are equal in size (Fig. S2c, rightmost column). As the resolution
54 is increased further, the channel side wall segments become smaller compared to the entrance and end wall
55 segments (Fig. S2d, rightmost column). The ratio of the channel entrance area to the area of a channel side
56 wall discretization segment S_0/S_i affects the rate of change in surface coverage $d\theta/dt$ (Eq. 14 in Ref. 1).

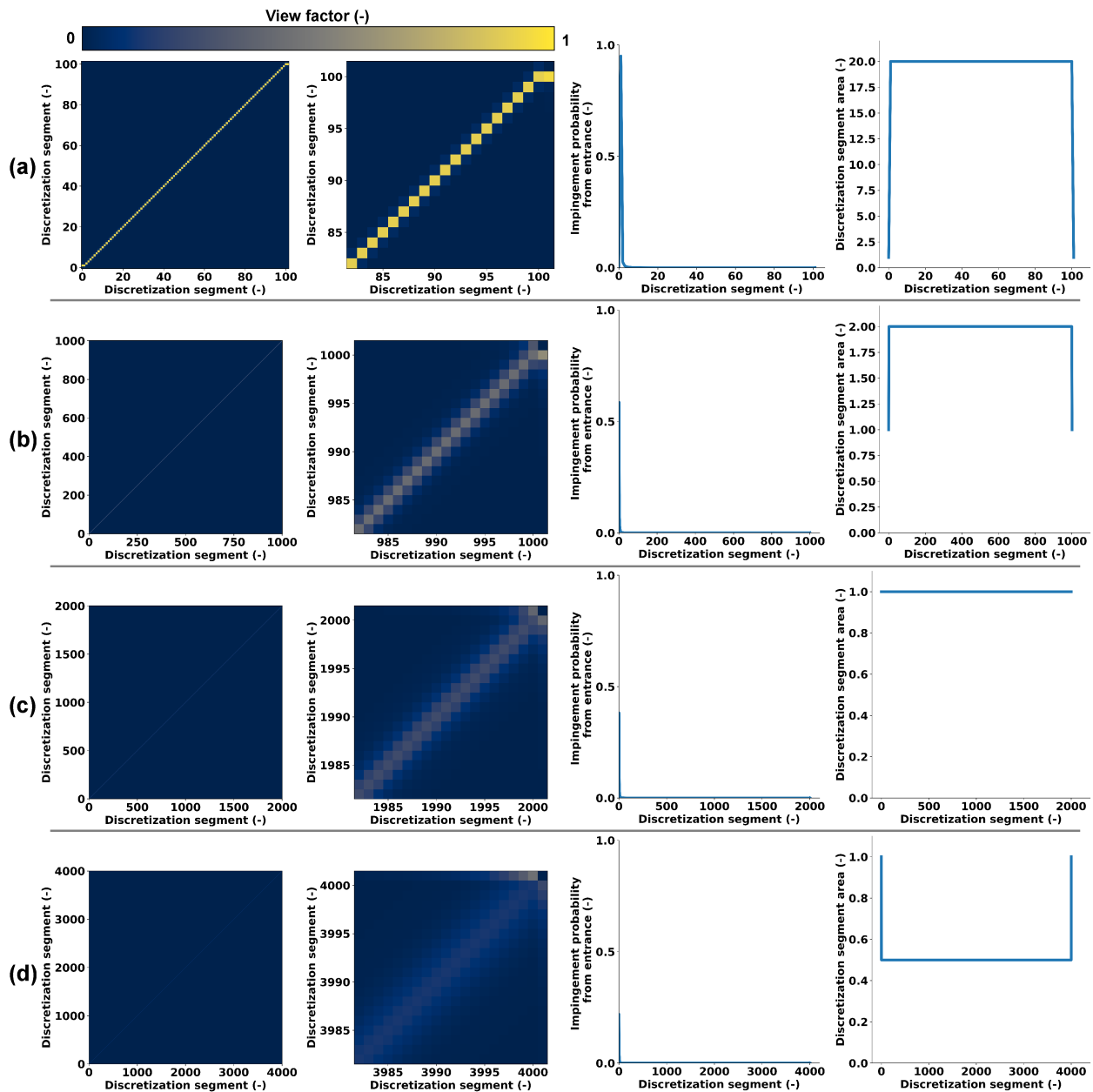


Figure S2 View factors between discretization segments, impingement probabilities from the channel entrance and segment areas for channels discretized into (a) 100, (b) 1000, (c) 2000 and (d) 4000 segments. The aspect ratio of the channel was 1000, which leads to a resolution of (a) 0.1, (b) 1, (c) 2 and (d) 4. The raster images (two leftmost columns) show the view factors between discretization segments in the whole channel and a zoomed-in view of the last 20 segments. The colour bar above the images indicates how the colours are mapped to the view factor values. The first discretization segment acts as the entrance of the channel, while the last segment marks the channel end wall. The plots (two rightmost columns) show the impingement probability from the channel entrance to each discretization segment and the area of each segment.

57 **References**

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